

**SMPS MOSFET**

IRFR15N20D  
 IRFU15N20D  
 HEXFET® Power MOSFET

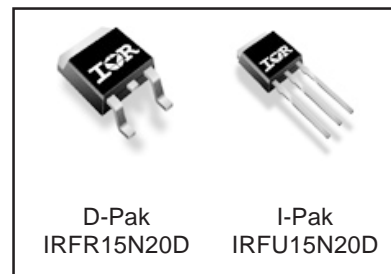
**Applications**

- High frequency DC-DC converters

$V_{DSS}$	$R_{DS(on) \max}$	$I_D$
200V	0.165Ω	17A

**Benefits**

- Low Gate-to-Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective  $C_{OSS}$  to Simplify Design, (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current



**Absolute Maximum Ratings**

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	17	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	12	
$I_{DM}$	Pulsed Drain Current ①	68	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	140	W
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation*	3.0	
	Linear Derating Factor	0.96	W/°C
$V_{GS}$	Gate-to-Source Voltage	± 30	V
$dv/dt$	Peak Diode Recovery $dv/dt$ ③	8.3	V/ns
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

**Thermal Resistance**

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.04	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)*	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

Notes ① through ⑤ are on page 10

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## Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	200	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.26	—	$V/^\circ\text{C}$	Reference to $25^\circ\text{C}$ , $I_D = 1\text{mA}$ ⑥
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.165	$\Omega$	$V_{GS} = 10V, I_D = 10A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.5	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	25	$\mu A$	$V_{DS} = 200V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 160V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 30V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -30V$

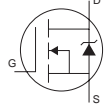
## Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$g_{fs}$	Forward Transconductance	4.0	—	—	S	$V_{DS} = 50V, I_D = 10A$
$Q_g$	Total Gate Charge	—	27	41	nC	$I_D = 10A$ $V_{DS} = 160V$ $V_{GS} = 10V, \text{④}$
$Q_{gs}$	Gate-to-Source Charge	—	6.9	10		
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	14	21		
$t_{d(on)}$	Turn-On Delay Time	—	9.7	—	ns	$V_{DD} = 100V$ $I_D = 10A$ $R_G = 6.8\Omega$ $V_{GS} = 10V$ ④
$t_r$	Rise Time	—	32	—		
$t_{d(off)}$	Turn-Off Delay Time	—	17	—		
$t_f$	Fall Time	—	8.9	—		
$C_{iss}$	Input Capacitance	—	910	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1.0\text{MHz}$ $V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$ $V_{GS} = 0V, V_{DS} = 160V, f = 1.0\text{MHz}$ $V_{GS} = 0V, V_{DS} = 0V \text{ to } 160V$ ⑤
$C_{oss}$	Output Capacitance	—	170	—		
$C_{riss}$	Reverse Transfer Capacitance	—	31	—		
$C_{oss}$	Output Capacitance	—	1380	—		
$C_{oss}$	Output Capacitance	—	67	—		
$C_{oss \text{ eff.}}$	Effective Output Capacitance	—	150	—		

## Avalanche Characteristics

	Parameter	Typ.	Max.	Units
$E_{AS}$	Single Pulse Avalanche Energy②	—	260	mJ
$I_{AR}$	Avalanche Current①	—	10	A
$E_{AR}$	Repetitive Avalanche Energy①	—	14	mJ

## Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	17	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	68		
$V_{SD}$	Diode Forward Voltage	—	—	1.5	V	$T_J = 25^\circ\text{C}, I_S = 10A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	130	200	ns	$T_J = 25^\circ\text{C}, I_F = 10A$
$Q_{rr}$	Reverse Recovery Charge	—	610	920	nC	$di/dt = 100A/\mu s$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ )				

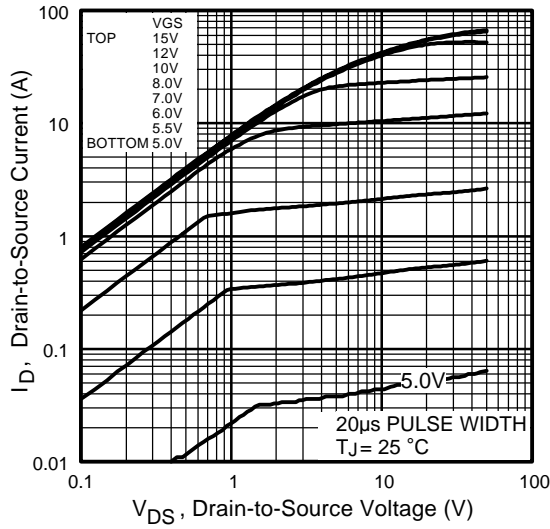


Fig 1. Typical Output Characteristics

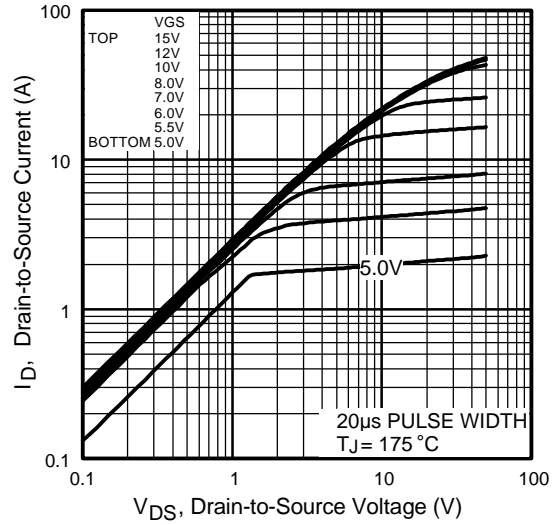


Fig 2. Typical Output Characteristics

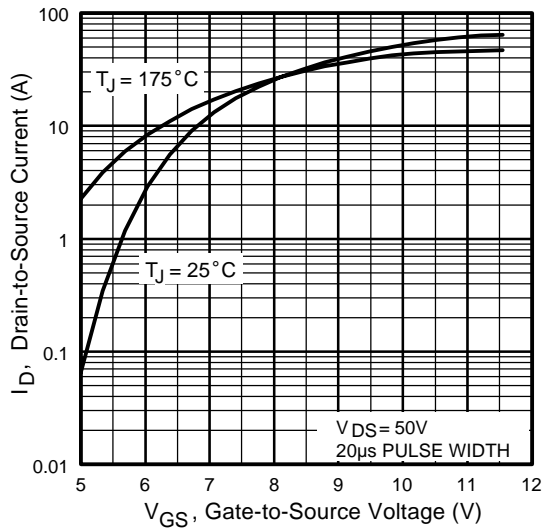


Fig 3. Typical Transfer Characteristics

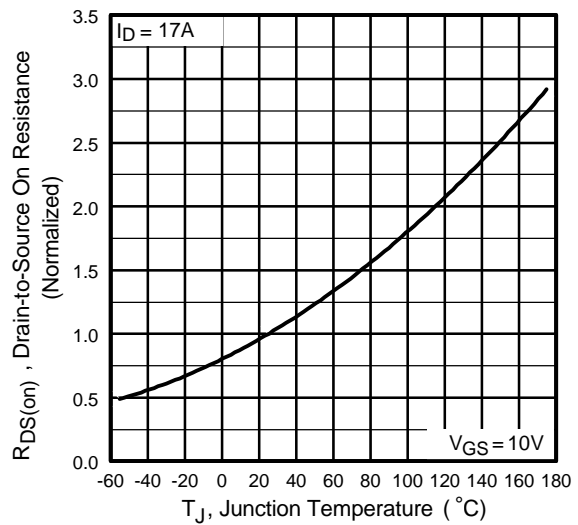
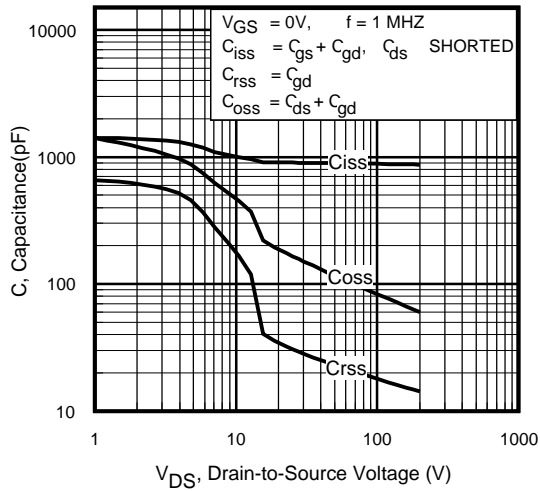
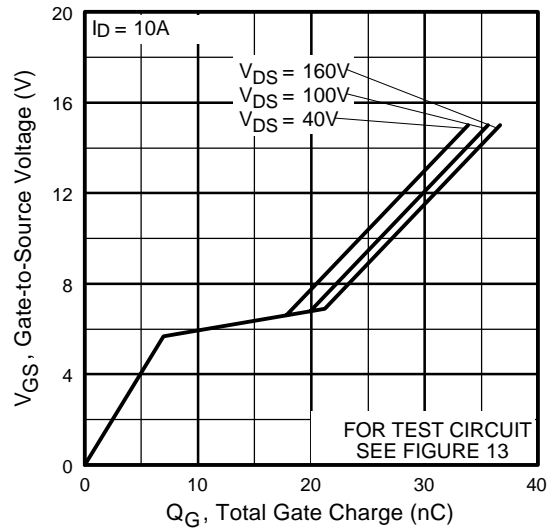


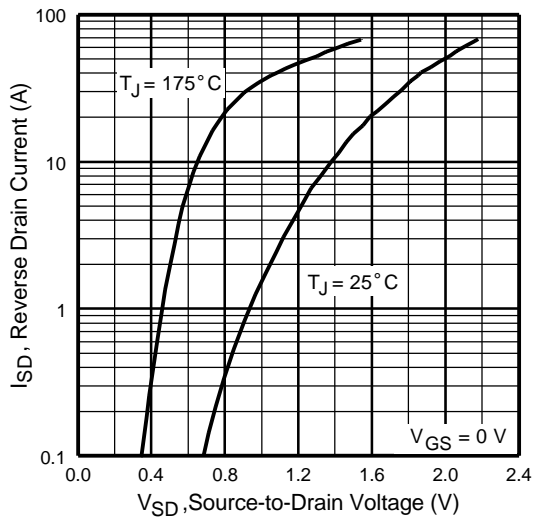
Fig 4. Normalized On-Resistance Vs. Temperature



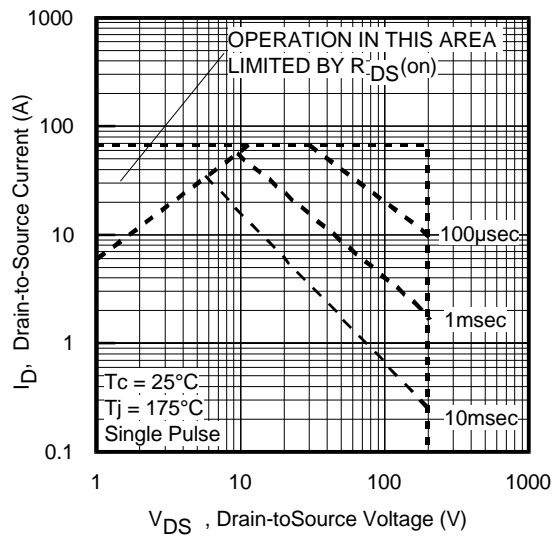
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



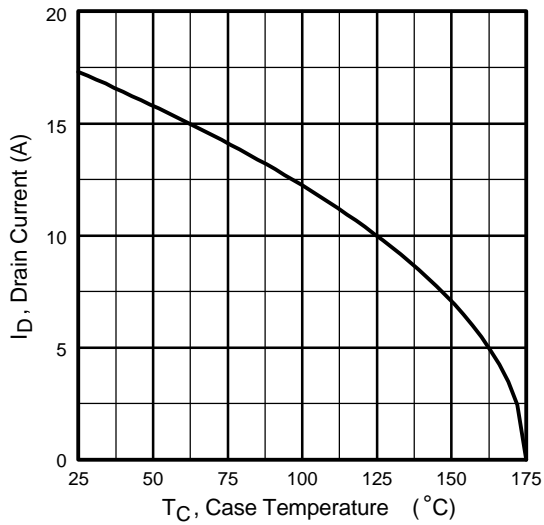
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



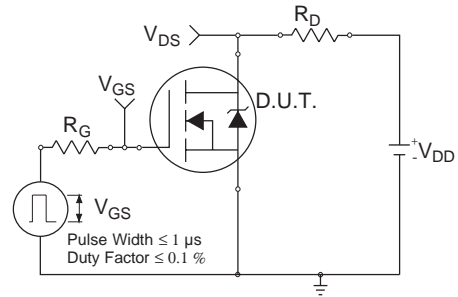
**Fig 7.** Typical Source-Drain Diode Forward Voltage



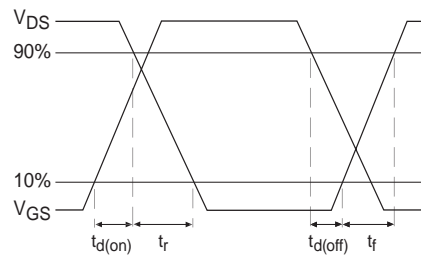
**Fig 8.** Maximum Safe Operating Area



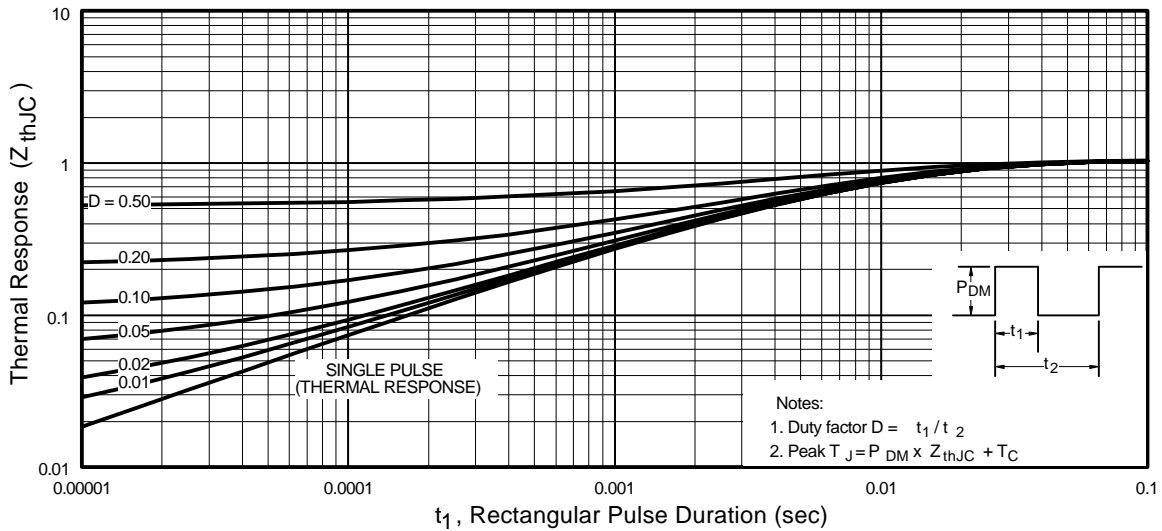
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



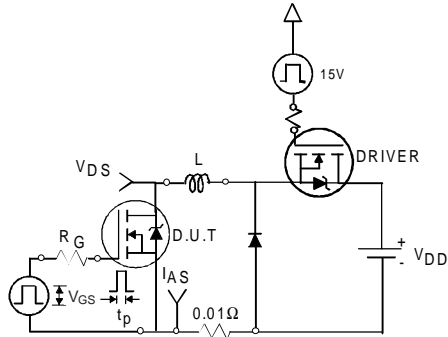
**Fig 10b.** Switching Time Waveforms



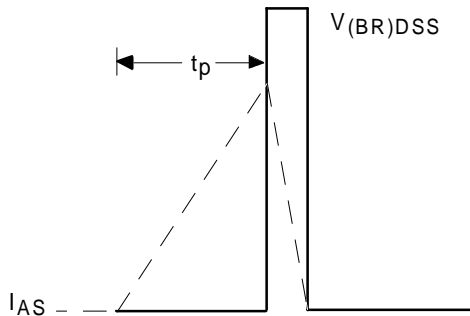
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

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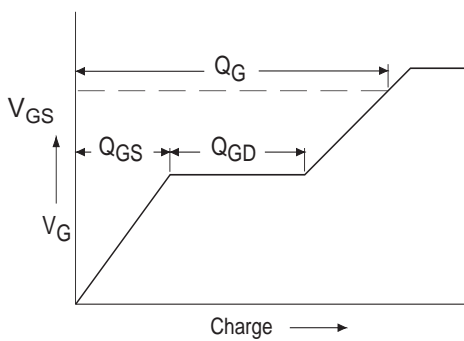
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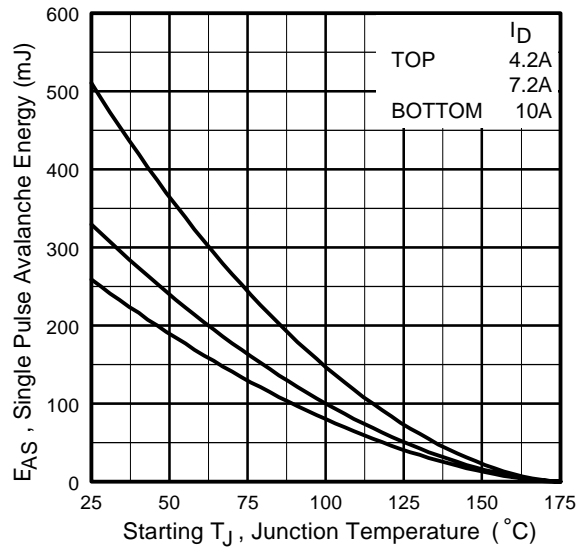
**Fig 12a.** Unclamped Inductive Test Circuit



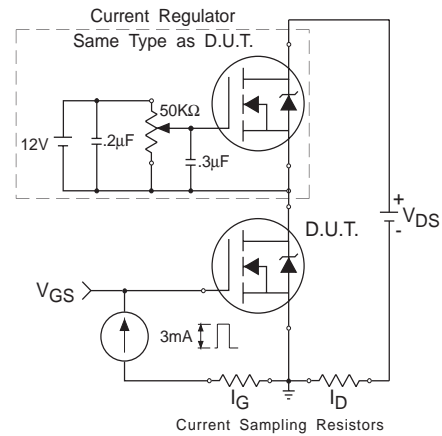
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 13a.** Basic Gate Charge Waveform

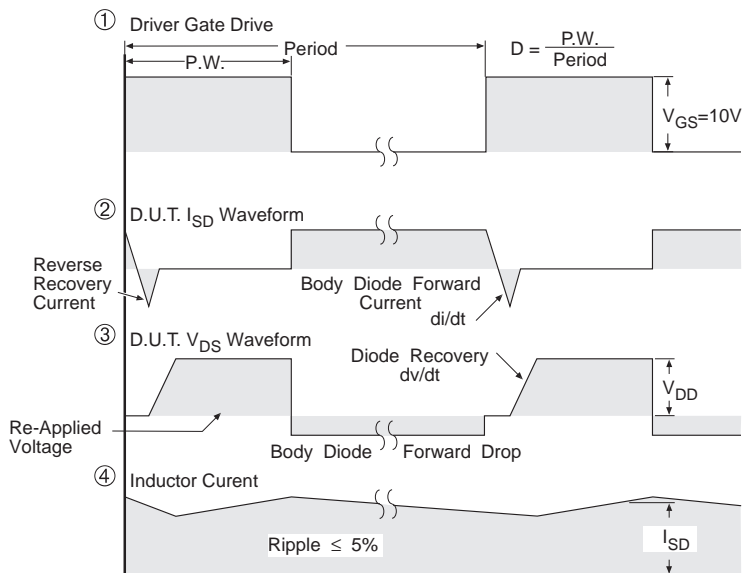


**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 13b.** Gate Charge Test Circuit

## Peak Diode Recovery dv/dt Test Circuit



\*  $V_{GS} = 5V$  for Logic Level Devices

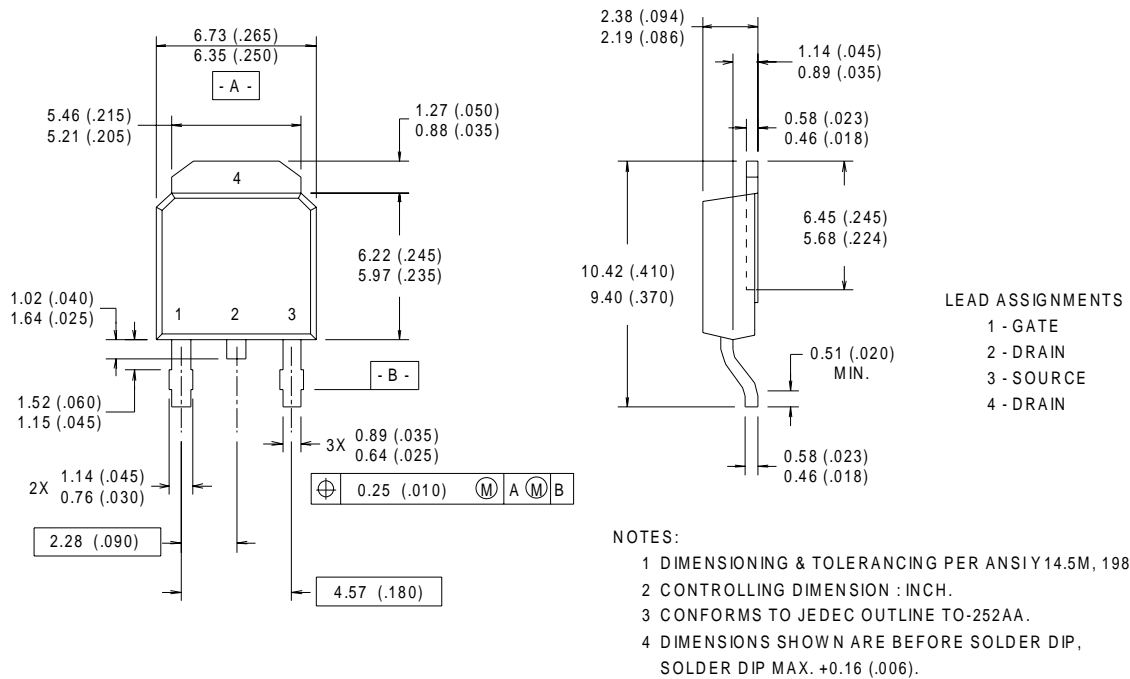
**Fig 14.** For N-Channel HEXFET® Power MOSFETs

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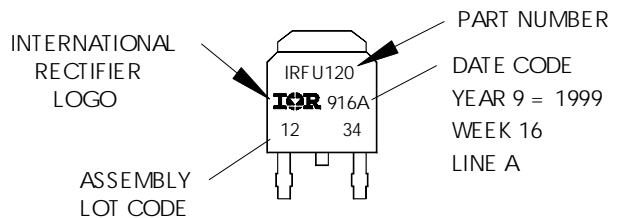
## D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



## D-Pak (TO-252AA) Part Marking Information

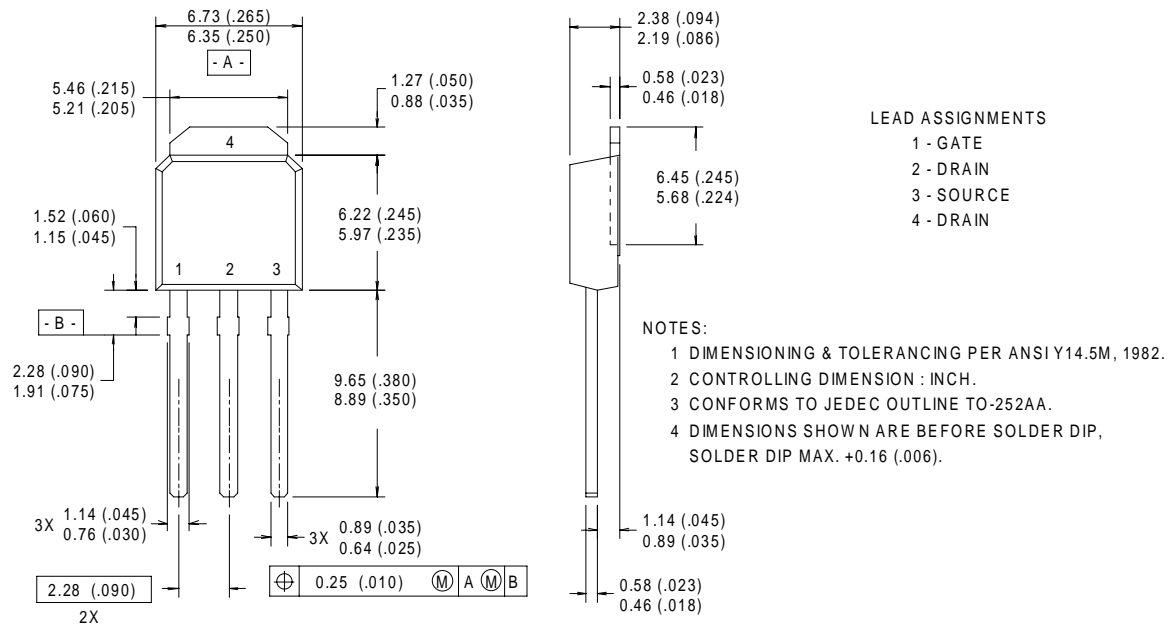
EXAMPLE: THIS IS AN IRFR120  
 WITH ASSEMBLY  
 LOT CODE 1234  
 ASSEMBLED ON WW 16, 1999  
 IN THE ASSEMBLY LINE "A"





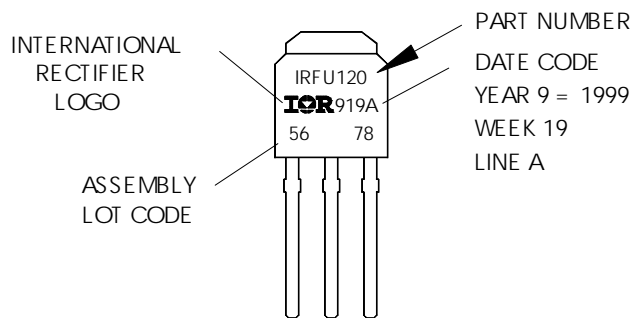
## I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



## I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120  
 WITH ASSEMBLY  
 LOT CODE 5678  
 ASSEMBLED ON WW 19, 1999  
 IN THE ASSEMBLY LINE "A"

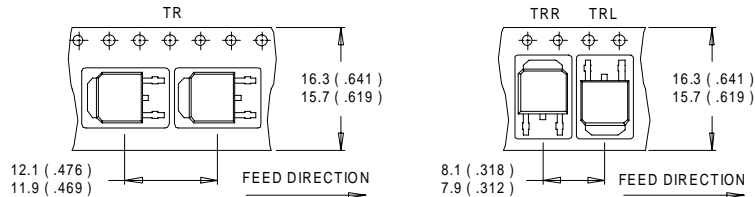


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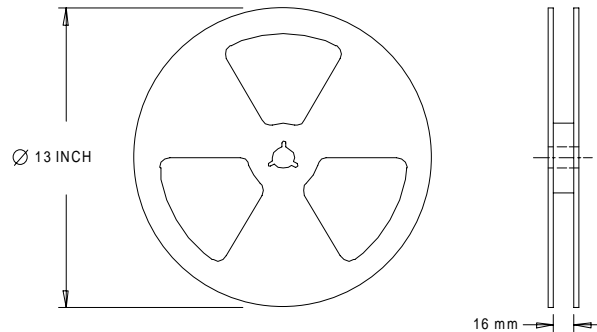
## D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



**NOTES :**

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



**NOTES :**

1. OUTLINE CONFORMS TO EIA-481.

**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
  - ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 4.9\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 10\text{A}$ .
  - ③  $I_{SD} \leq 10\text{A}$ ,  $di/dt \leq 170\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  
 $T_J \leq 175^\circ\text{C}$
  - ④ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
  - ⑤  $C_{oss}$  eff. is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$
- \* When mounted on 1" square PCB (FR-4 or G-10 Material).  
For recommended footprint and soldering techniques refer to application note #AN-994.

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Industrial market.  
Qualification Standards can be found on IR's Web site.

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